

# SILICON TRANSISTOR 2SC4958

# HIGH FREQUENCY LOW NOISE AMPLIFIER NPN SILICON EPITAXIAL TRANSISTOR SUPER MINI MOLD

## FEATURES

- Low Noise, High Gain
- Low Voltage Operation
- Low Feedback Capacitance Cre = 0.3 pF TYP.

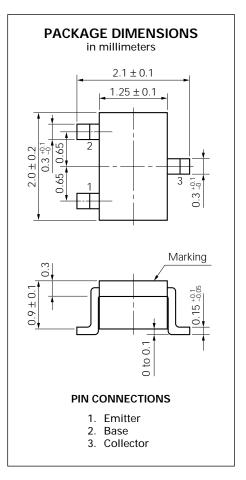
#### **ORDERING INFORMATION**

PART NUMBER	QUANTITY	PACKING STYLE
2SC4958-T1	3 Kpcs/Reel.	Embossed tape 8 mm wide. Pin3 (Collector) face to perfora- tion side of the tape.
2SC4958-T2	3 Kpcs/Reel.	Embossed tape 8 mm wide. Pin1 (Emitter), Pin2 (Base) face to perforation side of the tape.

\* Please contact with responsible NEC person, if you require evaluation sample. Unit sample quantity shall be 50 pcs. (Part No.: 2SC4958)

# ABSOLUTE MAXIMUM RATINGS (TA = 25 $^{\circ}$ C)

Collector to Base Voltage	Vсво	9	V
Collector to Emitter Voltage	Vceo	6	V
Emitter to Base Voltage	Vево	2	V
Collector Current	Ic	10	mA
Total Power Dissipation	Р⊤	60	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-65 to +150	°C



Caution; Electrostatic sensitive Device.

# ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Collector Cutoff Current	Ісво			0.1	μA	$V_{CB} = 5 V, I_E = 0$
Emitter Cutoff Current	Іево			0.1	μA	V <sub>EB</sub> = 1 V, Ic = 0
DC Current Gain	hfe	75		150		Vce = 3 V, Ic = 5 mA*1
Gain Bandwidth Product	f⊤		12		GHz	Vce = 3 V, Ic = 5 mA, f = 2.0 GHz
Feed back Capacitance	Cre		0.3	0.5	pF	Vсв = 3 V, IE = 0, f = 1 MHz <sup>*2</sup>
Insertion Power Gain	S21e  <sup>2</sup>	7	8.5		dB	Vce = 3 V, Ic = 5 mA, f = 2.0 GHz
Noise Figure	NF		2.5	4.0	dB	Vce = 3 V, Ic = 3 mA, f = 2.0 GHz

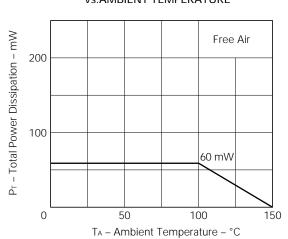
\*1 Pulse Measurement ; PW  $\leq$  350  $\mu$ s, Duty Cycle  $\leq$  2 % Pulsed.

\*2 Measured with 3 terminals bridge, Emitter and Case should be grounded.

#### hFE Classification

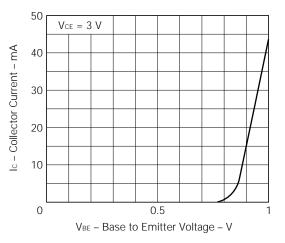
Rank	T82
Marking	T82
hfe	75 to 150

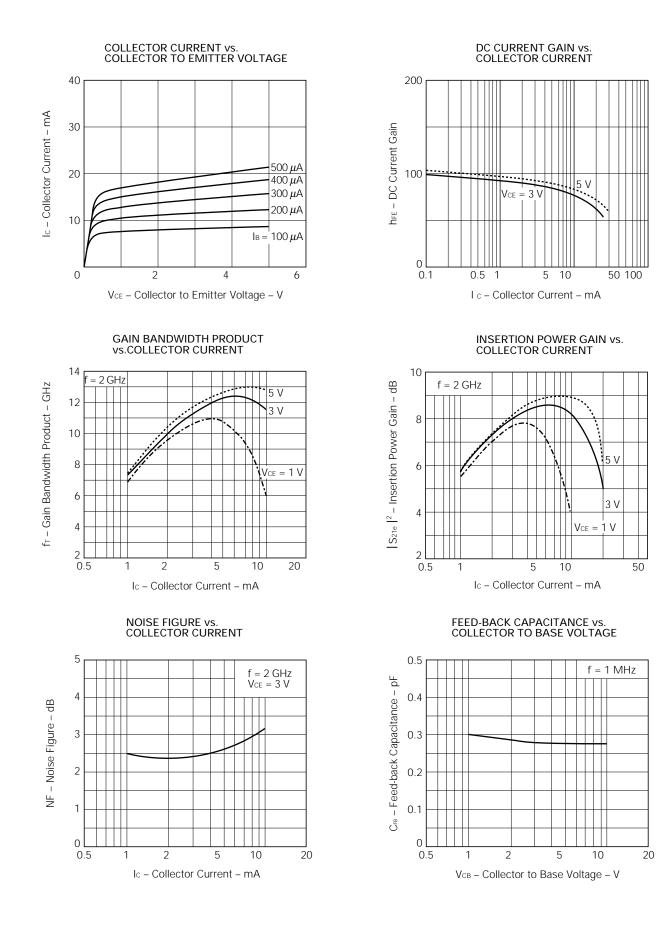
#### TYPICAL CHARACTERISTICS (TA = 25 °C)



# TOTAL POWER DISSIPATION vs.AMBIENT TEMPERATURE

#### COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE





# S-PARAMETER

(VCE = 3 V, IC = 1 mA, ZO = 50  $\Omega$ )

f	S11		Sa	<b>S</b> 21		<b>S</b> 12		<b>S</b> 22	
(GHz)	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG	
0.200	0.9410	-9.3	3.3070	167.3	0.0330	82.8	0.9900	-6.8	
0.400	0.9280	-17.7	3.1860	156.0	0.0650	78.5	0.9540	-13.7	
0.600	0.8670	-26.0	3.0130	144.9	0.0930	71.1	0.9250	-19.5	
0.800	0.8150	-33.6	2.8740	134.6	0.1160	67.0	0.8730	-24.9	
1.000	0.7280	-41.5	2.6360	124.4	0.1330	59.7	0.8250	-29.5	
1.200	0.6700	-47.3	2.5360	115.5	0.1480	59.1	0.7920	-33.6	
1.400	0.5970	-51.7	2.3840	107.7	0.1710	53.6	0.7640	-36.6	
1.600	0.5430	-56.3	2.2170	100.7	0.1820	52.0	0.7180	-39.9	
1.800	0.5040	-60.7	2.0650	95.0	0.1990	49.8	0.6810	-42.4	
2.000	0.4350	-64.4	2.0420	88.3	0.2040	51.6	0.6600	-46.9	
2.200	0.3920	-69.4	1.9690	82.0	0.2270	48.3	0.6210	-50.1	
2.400	0.3560	-71.5	1.8470	76.6	0.2320	50.1	0.6040	-51.8	
2.600	0.3240	-81.1	1.7690	71.1	0.2420	46.4	0.5840	-53.6	
2.800	0.3120	-76.7	1.7240	68.1	0.2520	45.1	0.5660	-57.6	
3.000	0.2450	-85.1	1.6690	63.2	0.2670	45.3	0.5410	-58.3	

# (VCE = 3 V, IC = 3 mA, Zo = 50 $\Omega$ )

f	S11		Sa	<b>S</b> 21		2	<b>S</b> 22	
(GHz)	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
0.200	0.8480	-15.9	7.7420	158.5	0.0320	79.4	0.9640	-11.3
0.400	0.7640	-27.6	6.8190	141.1	0.0560	68.2	0.8730	-20.5
0.600	0.6470	-37.3	5.8070	127.1	0.0770	66.9	0.7950	-26.1
0.800	0.5600	-44.1	5.0060	116.0	0.1000	64.5	0.7140	-30.2
1.000	0.4650	-49.4	4.2790	106.6	0.1110	64.1	0.6540	-33.0
1.200	0.4050	-51.9	3.8350	98.8	0.1250	62.2	0.6250	-34.4
1.400	0.3470	-53.4	3.4290	92.4	0.1340	62.6	0.5850	-36.3
1.600	0.3040	-55.0	3.0820	86.6	0.1570	60.9	0.5530	-38.2
1.800	0.2790	-55.7	2.7740	82.3	0.1840	60.8	0.5450	-39.3
2.000	0.2260	-53.6	2.6370	77.1	0.1910	57.5	0.5140	-42.2
2.200	0.2090	-57.9	2.4900	72.2	0.2090	59.4	0.5020	-45.3
2.400	0.1820	-53.8	2.2890	67.9	0.2260	58.1	0.4850	-46.1
2.600	0.1600	-67.3	2.1710	63.7	0.2280	53.4	0.4680	-47.9
2.800	0.1650	-58.5	2.0820	61.3	0.2580	57.0	0.4650	-51.6
3.000	0.1210	-51.3	2.0030	57.3	0.2670	52.6	0.4490	-51.4

## S-PARAMETER

(VCE = 3 V, IC = 5 mA, ZO = 50  $\Omega$ )

f	S11		S2	S21		S12		S22	
(GHz)	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG	
0.200	0.7750	-19.9	10.2330	153.0	0.0290	78.0	0.9310	-14.1	
0.400	0.6530	-32.4	8.4080	133.2	0.0560	66.1	0.8150	-23.3	
0.600	0.5270	-39.8	6.7610	119.0	0.0730	70.0	0.7170	-27.3	
0.800	0.4470	-45.7	5.5980	108.5	0.0880	67.6	0.6390	-30.3	
1.000	0.3590	-49.6	4.6700	100.0	0.1110	66.9	0.5950	-31.2	
1.200	0.3140	-50.3	4.1180	92.7	0.1230	67.5	0.5650	-32.4	
1.400	0.2790	-48.1	3.6300	87.1	0.1400	66.8	0.5450	-34.4	
1.600	0.2460	-46.9	3.2460	82.1	0.1540	64.1	0.5190	-35.9	
1.800	0.2190	-46.8	2.8850	78.1	0.1780	62.0	0.5210	-37.0	
2.000	0.1780	-43.6	2.7470	73.7	0.1940	62.9	0.5000	-38.9	
2.200	0.1650	-44.7	2.5810	68.8	0.2010	62.0	0.4780	-43.1	
2.400	0.1490	-37.6	2.3820	64.8	0.2240	60.1	0.4550	-43.1	
2.600	0.1370	-50.0	2.2440	61.4	0.2410	60.9	0.4710	-43.9	
2.800	0.1320	-47.6	2.1380	59.0	0.2530	57.7	0.4490	-47.9	
3.000	0.1030	-33.7	2.0440	55.3	0.2650	55.3	0.4380	-47.0	

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Anti-radioactive design is not implemented in this product.

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